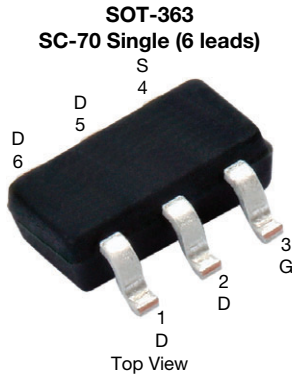


Automotive N-Channel 60 V (D-S) 175 °C MOSFET



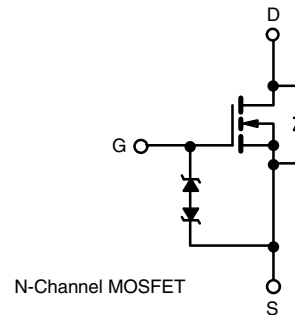
Marking code: 8B

PRODUCT SUMMARY	
V_{DS} (V)	60
$R_{DS(on)}$ (Ω) at $V_{GS} = 1.5$ V	1.41
I_D (A)	0.44
Configuration	Single
Package	SC-70

FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_g tested
- Typical ESD protection: 800 V
- Material categorization:
for definitions of compliance please see www.vishay.com/doc?99912

 AUTOMOTIVE
GRADE

RoHS
COMPLIANT
HALOGEN
FREE


ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-source voltage	V_{DS}	60	V	
Gate-source voltage	V_{GS}	± 8		
Continuous drain current ^a	I_D	$T_C = 25$ °C	0.44	A
		$T_C = 125$ °C	0.25	
Continuous source current (diode conduction) ^a	I_S	0.54		
Pulsed drain current ^b	I_{DM}	1.7		
Maximum power dissipation ^b	P_D	$T_C = 25$ °C	0.43	W
		$T_C = 125$ °C	0.14	
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +175	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction-to-ambient	R_{thJA}	460	°C/W	
Junction-to-foot (drain)				

Notes

- Package limited
- Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %
- When mounted on 1" square PCB (FR4 material)



SPECIFICATIONS ($T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0, I_D = 250\text{ }\mu\text{A}$		60	-	-	V
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		0.45	0.6	1	
Gate-source leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 3\text{ V}$		-	-	± 100	nA
		$V_{DS} = 0\text{ V}, V_{GS} = \pm 8\text{ V}$		-	-	100	
Zero gate voltage drain current	I_{DSS}	$V_{GS} = 0\text{ V}$	$V_{DS} = 60\text{ V}$	-	-	1	μA
		$V_{GS} = 0\text{ V}$	$V_{DS} = 60\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	-	50	
		$V_{GS} = 0\text{ V}$	$V_{DS} = 60\text{ V}, T_J = 175\text{ }^\circ\text{C}$	-	-	150	
On-state drain current ^a	$I_{D(on)}$	$V_{GS} = 1.5\text{ V}$	$V_{DS} \geq 5\text{ V}$	0.5	-	-	A
Drain-source on-state resistance ^a	$R_{DS(on)}$	$V_{GS} = 1.5\text{ V}$	$I_D = 2\text{ A}$	-	0.8	1.41	Ω
		$V_{GS} = 1.5\text{ V}$	$I_D = 1.2\text{ A}, T_J = 125\text{ }^\circ\text{C}$	-	-	2.4	
		$V_{GS} = 1.5\text{ V}$	$I_D = 1.2\text{ A}, T_J = 175\text{ }^\circ\text{C}$	-	-	3.1	
Forward transconductance ^b	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 1\text{ A}$		-	5.5	-	S
Dynamic ^b							
Input capacitance	C_{iss}	$V_{GS} = 0\text{ V}$	$V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	-	110	140	μF
Output capacitance	C_{oss}			-	19	24	
Reverse transfer capacitance	C_{rss}			-	12	15	
Total gate charge ^c	Q_g	$V_{GS} = 4.5\text{ V}$	$V_{DS} = 30\text{ V}, I_D = 2.8\text{ A}$	-	2.7	4.1	nC
Gate-source charge ^c	Q_{gs}			-	0.25	-	
Gate-drain charge ^c	Q_{gd}			-	0.35	-	
Gate resistance	R_g	$f = 1\text{ MHz}$		5.8	9	15.5	Ω
Turn-on delay time ^c	$t_{d(on)}$	$V_{DD} = 30\text{ V}, R_L = 30\text{ }\Omega$ $I_D \cong 1\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\text{ }\Omega$		-	12	18	ns
Rise time ^c	t_r			-	21	32	
Turn-off delay time ^c	$t_{d(off)}$			-	8	12	
Fall time ^c	t_f			-	7	11	
Source-Drain Diode Ratings and Characteristics ^b							
Pulsed current ^a	I_{SM}			-	-	1.6	A
Forward voltage	V_{SD}	$I_F = 0.8\text{ A}, V_{GS} = 0$		-	0.8	1.2	V

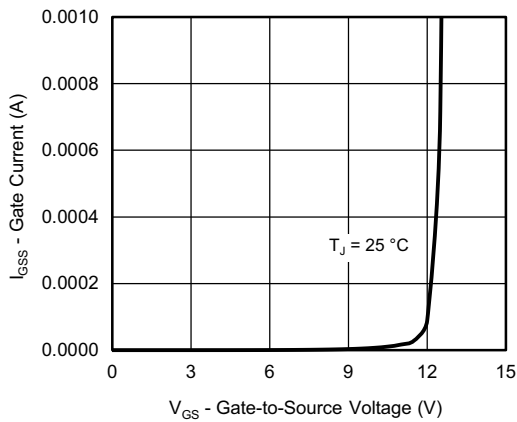
Notes

- Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
- Guaranteed by design, not subject to production testing.
- Independent of operating temperature

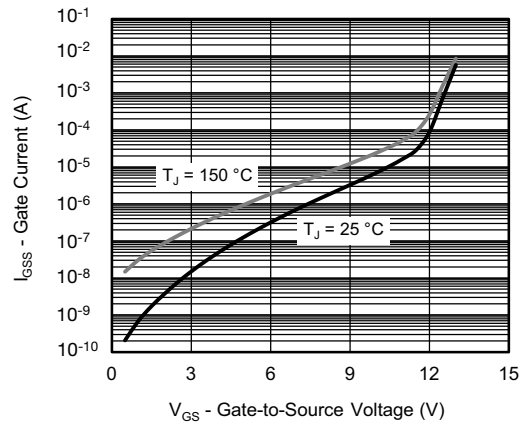
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



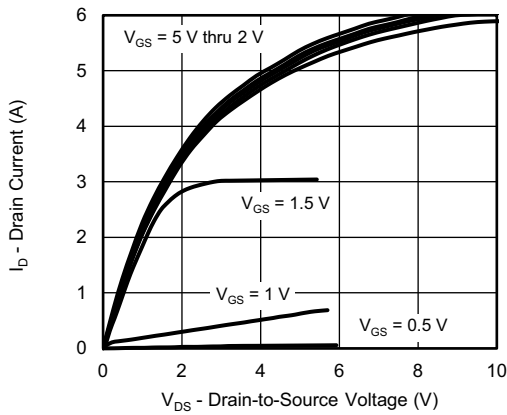
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



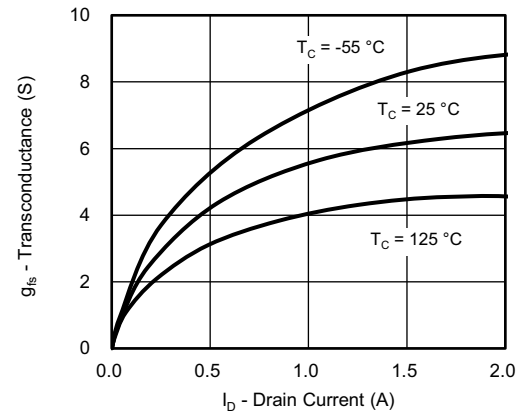
Gate Current vs. Gate-Source Voltage



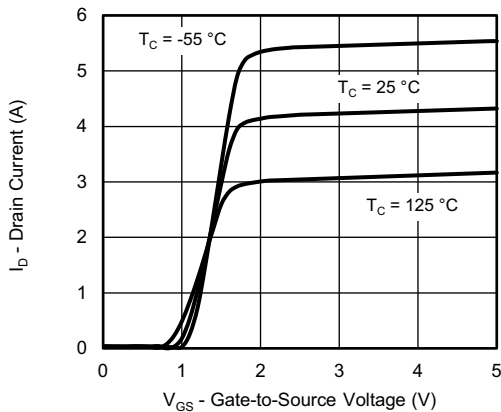
Gate Current vs. Gate-Source Voltage



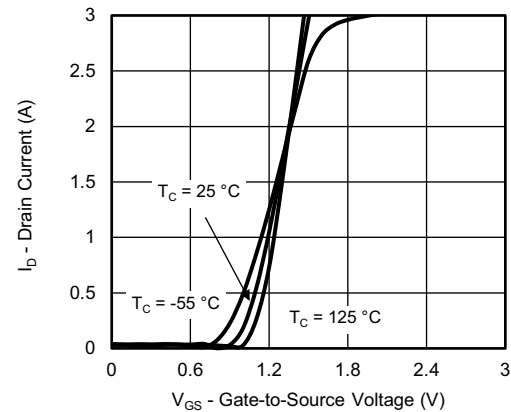
Output Characteristics



Transconductance



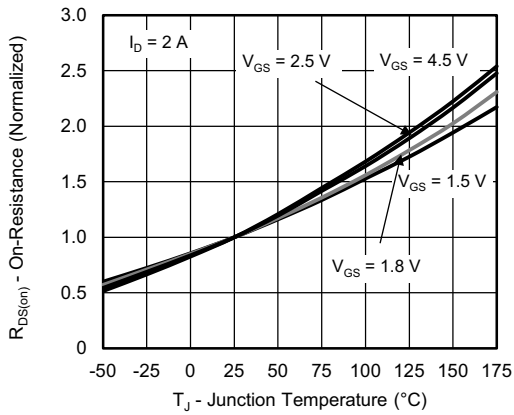
Transfer Characteristics



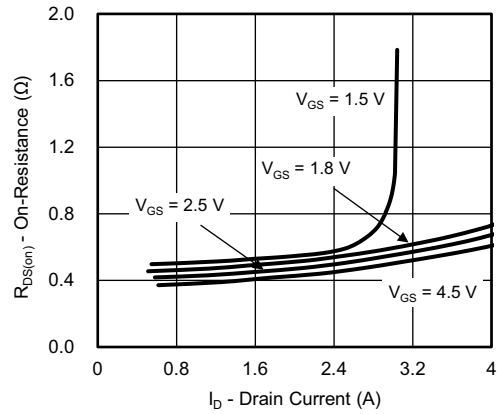
Transfer Characteristics



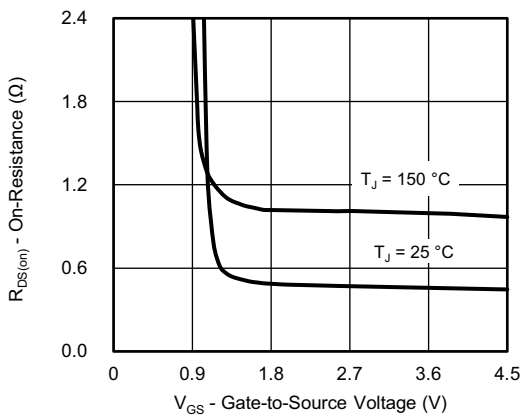
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



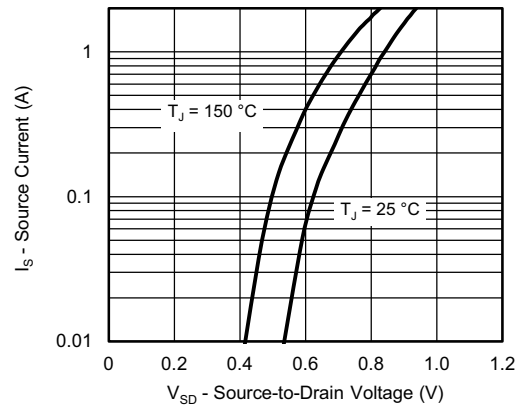
On-Resistance vs. Junction Temperature



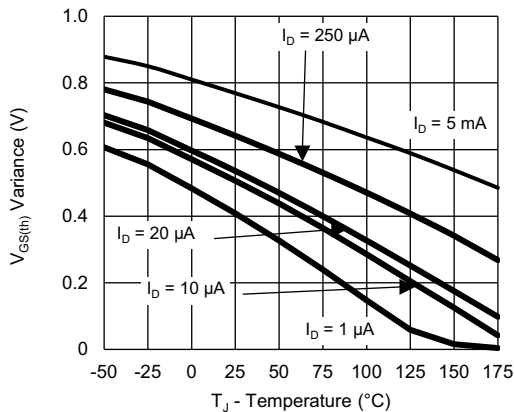
On-Resistance vs. Drain Current



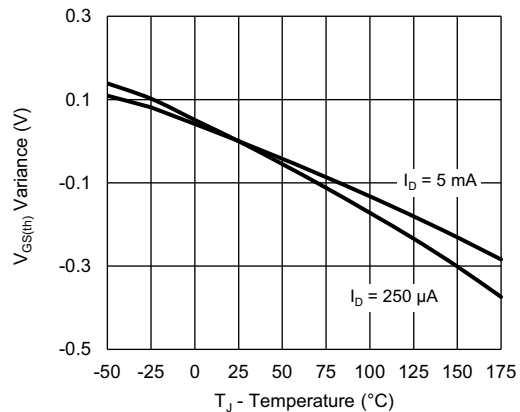
On-Resistance vs. Gate-to-Source Voltage



Source Drain Diode Forward Voltage



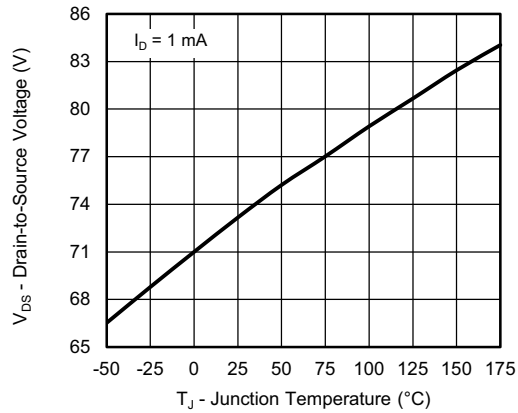
Threshold Voltage



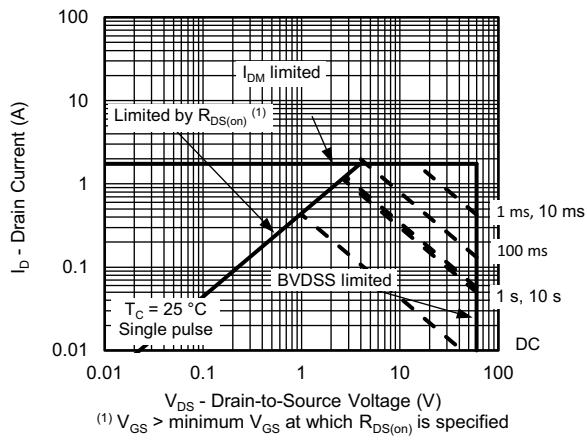
Threshold Voltage



TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)

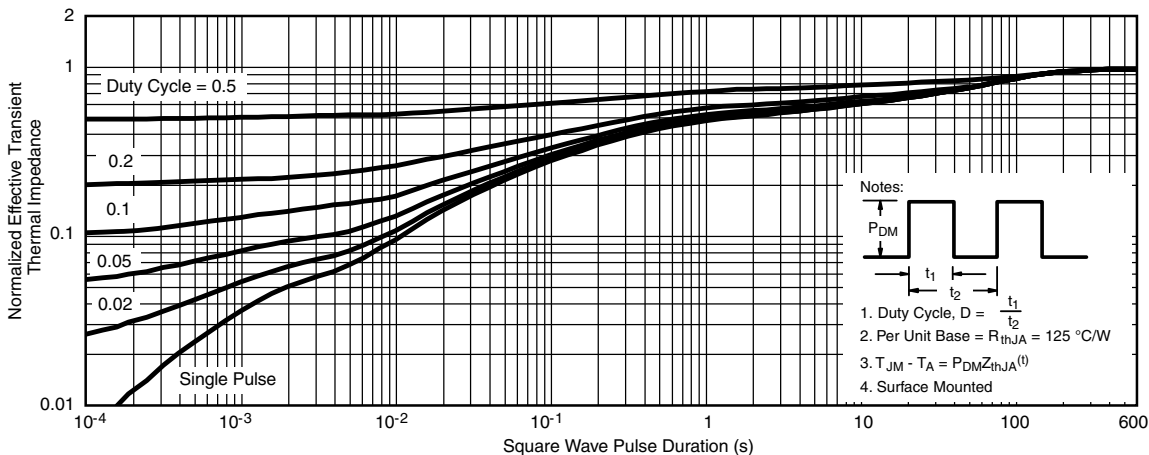


Drain Source Breakdown vs. Junction Temperature

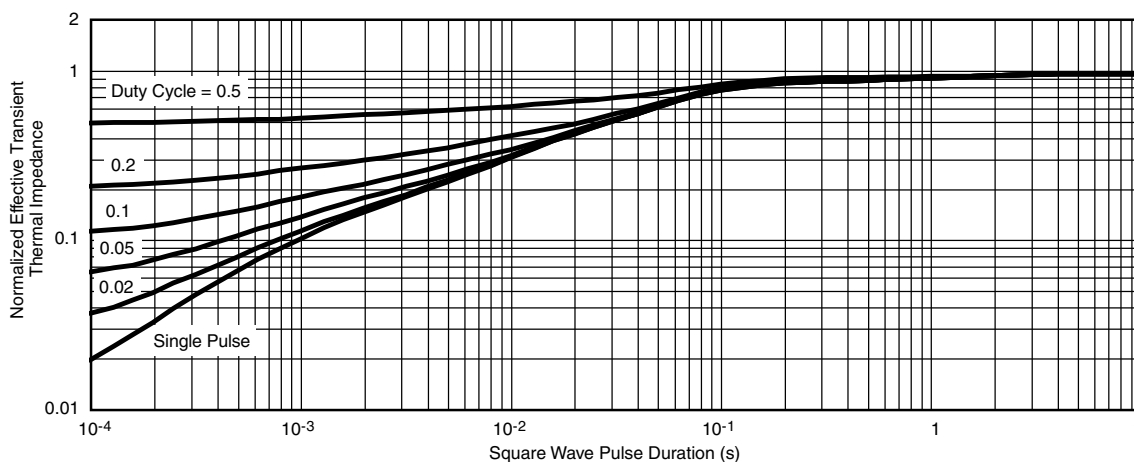




THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



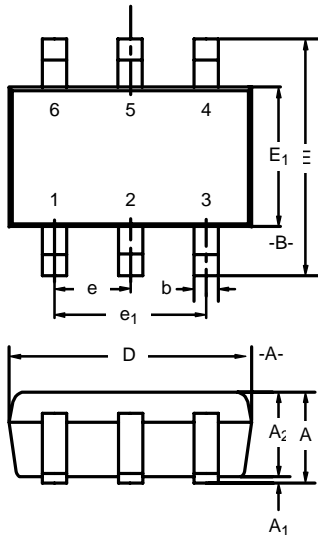
Normalized Thermal Transient Impedance, Junction-to-Foot

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^\circ\text{C}$)
 - Normalized Transient Thermal Impedance Junction-to-Foot ($25\text{ }^\circ\text{C}$)
 are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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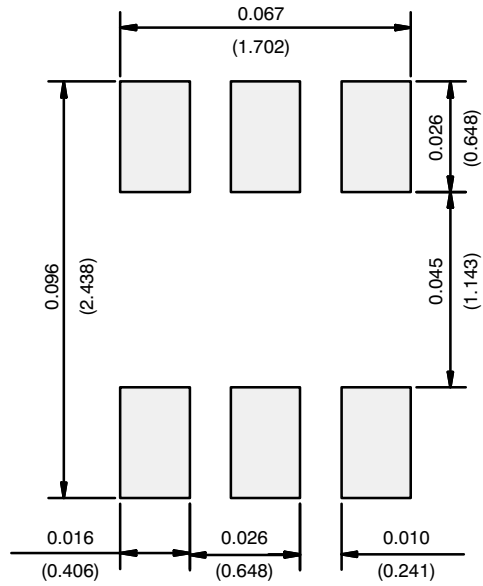
SC-70: 6-LEADS



Dim	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max
A	0.90	-	1.10	0.035	-	0.043
A ₁	-	-	0.10	-	-	0.004
A ₂	0.80	-	1.00	0.031	-	0.039
b	0.15	-	0.30	0.006	-	0.012
c	0.10	-	0.25	0.004	-	0.010
D	1.80	2.00	2.20	0.071	0.079	0.087
E	1.80	2.10	2.40	0.071	0.083	0.094
E ₁	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65BSC			0.026BSC		
e ₁	1.20	1.30	1.40	0.047	0.051	0.055
L	0.10	0.20	0.30	0.004	0.008	0.012
α	7°Nom			7°Nom		

ECN: S-03946—Rev. B, 09-Jul-01
DWG: 5550

RECOMMENDED MINIMUM PADS FOR SC-70: 6-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

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